## On the Nucleation of Microcracks in Metals under External Loading

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In earlier works [1,2] was suggested a theory of formation of nuclei of vacancy clusters in a single crystal metal subject to the uniaxial strain. After ascuming an analogy with the process of formation of a new phase in a liquid-vapour system, the nucleation rate equation was derived. On the basis of energy considerations the change of the activation energy of the vacancy motion, due to the crystal elongation, was also found in the form

$$\Delta U = aR_0^{-m} \left\{ 1 - (1+\epsilon)^{-m} - \frac{m}{n} \left[ 1 - (1+\epsilon)^{-n} \right] \right\} , \qquad (1)$$

where a, m, n, are material constants,  $\epsilon$  is the linear strain of the crystal, and  $R_0$  is the lattice constant.

The aim of the paper is to investigate the microcrack nucleation rate in a polycrystalline metal subject to the uniaxial strain. As it is known, the vacancy clusters are formed much easier on the grain boundaries than within the grains. Thus, one of the ways which can bring us closer to the early stage of fracture mechanism consists in investigating the process of heterogeneous nucleation of the microcrack. The considerations are based on assuming an analogy with the process of vapour condensation on a substrate. On the other hand, the treatment of heterogeneous nucleation requires an atomistic approach since in our case very high supersaturations are expected. Consequently, for the analysis of the problem the description of vapour deposits on a substrate, carried out on the basis of

Let us consider a sample of a polycrystal subject to the uniaxial strain. The assumptions may be listed as follows:

(i) Dislocation density is negligibly small everywhere except on the grain boundaries. (ii) Grain boundaries are free from preferential adsorption sites. (iii) Only single advacancies (adsorbed vacancies) are mobile on the grain boundaries. (iv) Only single advacancies may desorb directly from the boundaries. (v) Aggregate nucleation and growth coour only by the addition of single vacancies due to the surface diffusion. (vi) A quasi-steady state is established.

Let us now consider an internal region of the crystal containing a grain boundary. The problem has been analysed via the petit canonical ensamble and reduced to that of calculating the partition function of a two-dimensional adsorbed gas composed of different aggregates.

The partition function has the form

$$Z = \sum_{i} \exp \left(-\frac{E_{i}}{kT}\right)$$

where  $\mathbf{E}_{\mathbf{i}}$ s the energy of state i,k is Boltzmann's constant,  $\mathbf{T}$  is the absolute temperature, and the sum is taken over all possible configurations of the N advacancies on the grain boundary.

Let N<sub>o</sub> be the density of discrete adsorption sites per unit area of the boundary ( $\approx 10^{15} {\rm cm}^{-2}$ ), N<sub>n</sub> - the equilibrium surface density of clusters of n advacancies, and  $\epsilon_n$  - the potential energy of an aggregate of size n. Assuming that N<sub>o</sub>  $\gg \sum_{i=1}^{n}$  N<sub>i</sub>, N<sub>i</sub> aggregates can be distributed over N<sub>o</sub> positions in

$$\binom{N_0}{N_1} = \frac{N_0(N_0-1)...(N_0-N_1+1)}{N_1!} \approx \frac{1}{N_1!} N_0^{N_1}$$
 ways,

and its contribution to the partition function is

$$T_{i} = (1/N_{i})N_{0}^{N_{i}} \exp(N_{i} \epsilon_{i}/kT) . \qquad (2)$$

The total contribution to Z of all the aggregates is the product of all the terms (2), and the partition function is the sum of all these products over all possible distributions

$$Z = \sum_{k=1}^{n} \prod_{i=1}^{k} \frac{1}{N_{i}!} \left[ N_{o} \exp(\frac{\epsilon_{1}}{kT}) \right]^{N_{i}}$$
(3)

The most probable distribution of aggregates  $N_n$  corresponds to the minimum of free energy F. This, owing to the relation F=-kTlnZ, leads to the maximum of lnZ with the condition

$$\sum_{i=1}^{n} iN_{i} = N \tag{4}$$

Thus, the problem is reduced to the solution of a set of two equations: (4) and

$$\frac{\partial}{\partial \mathbf{N}_{\mathbf{j}}} \left[ \ln \mathbf{Z} + \ln \lambda \left( \sum_{i=1}^{n} i \mathbf{N}_{i} - \mathbf{N} \right) \right] = 0$$
 (5)

where  $\ln \lambda$  is the Lagrangian multiplier.

Replacing the sum (3) by the largest component T (the method of the maximum term), assuming that  $N_i \gg 1$  and applying Stirling's formula  $\ln N_i! = N_i \ln N_i - N_i$ , we obtain

$$\operatorname{lnT=\ln \prod_{i=1}^{n} \frac{1}{N_{i}!} \left[ N_{o} \exp\left(\frac{\epsilon_{i}}{kT}\right) \right]^{N_{i}} = \sum_{i=1}^{n} \left[ -N_{i} \ln N_{i} + N_{i} + N_{i} \left( \ln N_{o} + \frac{\epsilon_{i}}{kT} \right) \right] (6)}$$

Formal differentiating of Eq.(5), Eq.(6) being taken into account, leads to

$$\frac{\partial}{\partial \mathbf{N}_{\mathbf{j}}} \left[ \ln \mathbf{T} + \ln \lambda \left( \sum_{i=1}^{n} i \mathbf{N}_{i} - \mathbf{N} \right) \right] = + \ln \mathbf{N}_{0} + \frac{\epsilon_{\mathbf{j}}}{k \mathbf{T}} + j \ln \lambda - \ln \mathbf{N}_{\mathbf{j}} = 0$$
 (7)

Hence,  $N_j = N_0 \exp(\epsilon_j/kT) \lambda^j$  and putting j=1 we can find  $\lambda$  and the density of critical clusters  $N_{n,r}$ 

$$N_{n*} = B_0(N_1/B_0)^{n*} \exp(E_{n*}/kT)$$
, (8)

where n' is the number of advacancies in a critical cluster, and  $\mathbb{E}_{n^*} = \mathbb{E}_{n^*} = \mathbb{E}_1$  is the net gain in energy when the cluster is formed from n\* advacancies (binding energy).

The nucleation rate J is the rate of promotion of critical clusters, containing n\* vacancies, to the smallest stable clusters (nuclei) by advacancy capture

$$J = N_{D^*} N_{D^*} , \qquad (9)$$

where  $w_{n*}$  is the capture rate of single advacancies by a cluster of size  $n^*$ .

The mean lifetime of an advacancy before description is  $\Upsilon_a^{-}$   $\gamma^{-1} \exp(E_a/kT)$  where  $\gamma \approx 10^{13}$  is the atomic vibrational frequency, and  $E_a$  is the adsorption energy of a single vacancy. If we denote by  $P_p$  the incidence rate of vacancies, the equilibrium advacancy population  $N_1$  can be expressed as

$$^{\rm N}_{\rm l} = {\rm P}_{\rm p}^{\gamma} {\rm a} = {\rm P}_{\rm p}^{\gamma-1} \exp({\rm E}_{\rm a}/{\rm kT}) \tag{10}$$

The incidence rate may be written approximately as  $P_p = vc$ , where v is the avarage velocity of a vacancy which can be determined as  $v = vR_0 \exp \left[-(U_m - \Delta U)/kT\right]$  with  $U_m$  denoting the activation energy of motion of vacancies and  $\Delta U$  given by (1); c is the current volume vacancy concentration in the strained crystal ( $\epsilon > 0$ ). On the other hand, the initial concentration of vacancies ( $\epsilon = 0$ ) is given by the known formula  $c_0 = N \exp \left(-U_f/kT\right)$ , where N is the total number of atomic sites per unit volume and  $U_f$  is the activation energy of formation of a vacancy. If we assume that, due to the

strain, this energy will be lowered by  $\Delta U$ , then  $c = \mathcal{N} \exp \left[-(U_{\hat{\mathbf{I}}} - \Delta U)/kT\right] = c_0 \exp(\Delta U/kT)$ . Thus, the incidence rate is  $P_p = yR_0 c_0 \exp \left[-(U_m - 2\Delta U)/kT\right] \ . \tag{11}$ 

The capture rate  $w_{n*}$  can be reckened from kinetic considerations. When advacancies diffuse over the grain boundary with a mean velocity  $v_d$  discreption  $v_d$  discreption sites and  $v_d$  is the activation energy for surface diffusion, and  $v_d$  is the capture width of the critical aggregate, then

$$w_{n*} = b_{n*} dyN_1 exp(-E_d/kT)$$
 (12)

Substituting (8) and (12) into (9) and taking into account (10) and (11) as well as putting  $N_o \approx 1/d^2$ , we finally obtain the microcrack nucleation rate in the loaded crystal

$$J=(R_0c_0)^{n^*+1}d^{2n^*-1}b_{n^*} \exp\left\{\left(n^*+1\right)\left(E_a-U_m+2\Delta U\right)+E_{n^*}-E_d\right]/kT\right\}$$
 (13) where  $\Delta U$ , as a function of strain  $\varepsilon$ , is given by (1).

The proposed mechanism of microcrack nucleation explains to some degree the beginning of the process of fracture and the nature of formation of small cracks. Once the growing nucleus of a microcrack has reached the size of the order of a Griffith crack, its further growth can follow the existing continuum hypotheses.

## References

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